

FDN337N

N-Channel Logic Level Enhancement Mode Field Effect Transistor

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Product Summary

BVDSS	RDSON	ID
30 V	55 mΩ	2.2A

Application

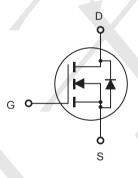
- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

Package and Pin Configuration

SOT-23



Circuit diagram



Marking:



Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V _{DS}	30	V	
Gate-Source Voltage	V_{GS}	±8	v	
Drain Current(continuous)	I_D	2.2	۸	
Drain Current(pulsed)	I _{DM}	10	A	
Power Dissipation	P _D	0.5	W	
Thermal Resistance from Junction to Ambient (t≤5s)	$R_{\theta JA}$	625	°CM	
Operating Junction	TJ	150	°C	
Storage Temperature	T _{STG}	-55 ~+150		



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Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit	
Static Characteristics							
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =10μA	30			_ v	
Gate-threshold voltage	VGS(th)	$V_{DS} = V_{GS}$, $I_D = 50\mu A$ 0.			1		
Gate-body leakage	I _{GSS}	V _{DS} =0V, V _{GS} =±8V			±100	nA	
Zero gate voltage drain current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	μA	
Drain-source on-resistance ¹	D	V _{GS} =4.5V, I _D =2.2A		0.055	0.065	Ω	
	RDS(on)	Vgs =2.5V, Ip =2A		0.070	0.090		
Forward transconductance ¹	G fs	V _{DS} =5V, I _D =3.6A		8		S	
Diode forward voltage	V _{SD}	I _S =0.94A,V _{GS} =0V			1.2	V	
	•		/				
Input capacitance 2	C _{iss}			300			
Output capacitance ²	Coss	V _{DS} =10V,V _{GS} =0V,f=1MHz		120		pF	
Reverse transfer capacitance ²	C _{rss}			80			
Switching Characteristics ²	•			•	•		
Turn-on delay time	$\mathbf{t}_{d_{(on)}}$	- VDS=5V VGS=4.5V Rgen=6Ω -		7		ns	
Turn-off delay time	t d(off)			15			

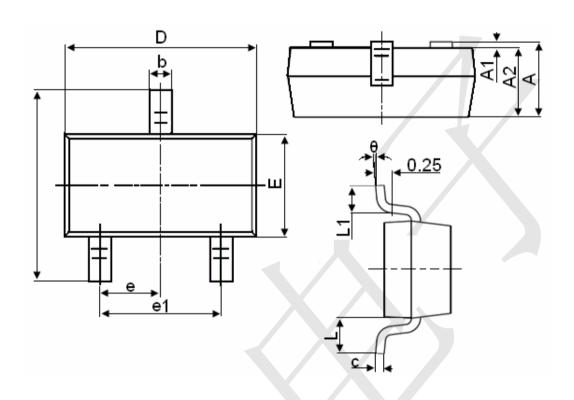


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SOT-23 Package Information



Symbol		Dimensions in Millimeters	
Syllibol	MIN.	MAX.	
Α	0.900	1.150	
A1	0.000	0.100	
A2	0.900	1.050	
b	0.300	0.500	
С	0.080	0.150	
D	2.800	3.000	
E	1.200	1.400	
E1	2.250	2.550	
е	0.950TYP		
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.500	
θ	0°	8°	

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